

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (Ultra High speed U-MOSIII)

TENTATIVE

TPCA8014-H

High Speed and High Efficiency DC-DC Converters
 Notebook PC Applications
 Portable Equipment Applications

- Small footprint due to small and thin package
- High speed switching
- Small gate charge: $Q_{sw} = 7.4 \text{ nC (typ.)}$
- Low drain-source ON resistance: $R_{DS(ON)} = 10.5 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance: $|Y_{fs}| = \text{TBD S (typ.)}$
- Low leakage current: $I_{DSS} = 10 \mu\text{A (max)} \text{ (} V_{DS} = 40 \text{ V)}$
- Enhancement mode: $V_{th} = 1.1 \text{ to } 2.3 \text{ V (} V_{DS} = 10 \text{ V, } I_D = 1 \text{ mA)}$

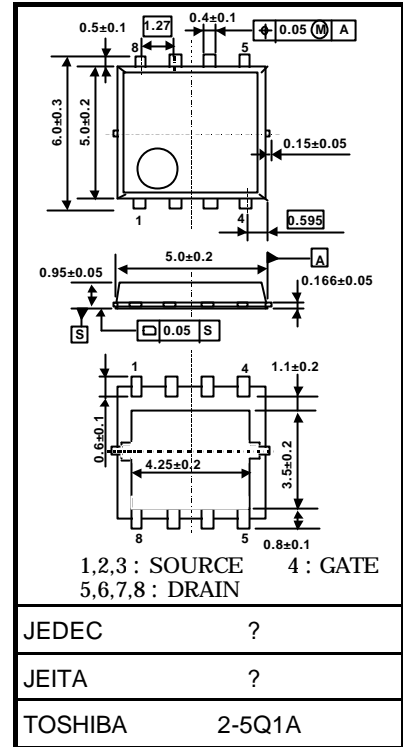
Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	40	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	40	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	30	A
	Pulsed (Note 1)	I_{DP}	90	
Drain power dissipation ($T_c=25^\circ\text{C}$)		P_D	45	W
Drain power dissipation ($t = 10 \text{ s}$) (Note 2a)		P_D	2.8	W
Drain power dissipation ($t = 10 \text{ s}$) (Note 2b)		P_D	1.6	W
Single pulse avalanche energy (Note 3)		E_{AS}	84	mJ
Avalanche current		I_{AR}	30	A
Repetitive avalanche energy ($T_c=25^\circ\text{C}$) (Note 4)		E_{AR}	TBD	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	-55 to 150	°C

Note: For (Note 1), (Note 2), (Note 3), (Note 4), please refer to the next page.

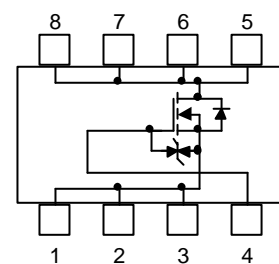
This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm



Weight: 0.080 g (typ.)

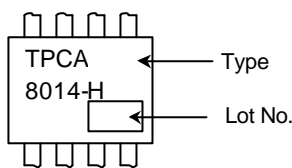
Circuit Configuration



Thermal Characteristics

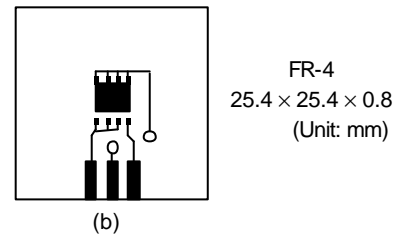
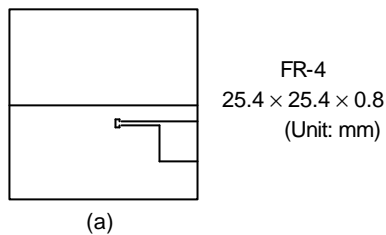
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case ($T_c=25$)	$R_{th (ch-c)}$	2.78	$^{\circ}C/W$
Thermal resistance, channel to ambient ($t = 10$ s) (Note 2a)	$R_{th (ch-a)}$	44.6	$^{\circ}C/W$
Thermal resistance, channel to ambient ($t = 10$ s) (Note 2b)	$R_{th (ch-a)}$	78.1	$^{\circ}C/W$

Marking (Note 5)



Note 1: Please use devices on condition that the channel temperature is below $150^{\circ}C$.

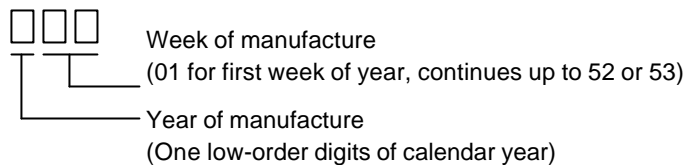
Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



Note 3: $V_{DD} = 24$ V, $T_{ch} = 25^{\circ}C$ (initial), $L = 0.1$ mH, $R_G = 25$ Ω , $I_{AR} = 30$ A

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: * Weekly code: (Three digits)



Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA
Drain cut-OFF current		I_{DSS}	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$	—	—	10	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	40	—	—	V
		$V_{(BR)DSX}$	$I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$	25	—	—	
Gate threshold voltage		V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.1	—	2.3	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$	—	7.0	9.5	$\text{m}\Omega$
			$V_{GS} = 4.5\text{ V}, I_D = 15\text{ A}$	—	10.5	15	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 15\text{ A}$	TBD	TBD	—	S
Input capacitance		C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	1365	—	pF
Reverse transfer capacitance		C_{rss}		—	110	—	
Output capacitance		C_{oss}		—	500	—	
Gate resistance		R_g		—	1.0	—	
Switching time	Rise time	t_r	<p>$V_{GS} = 10\text{ V}$ 0 V $I_D = 15\text{ A}$ V_{OUT} 4.7Ω $R_L = 1.33\Omega$ $V_{DD} = 20\text{ V}$ Duty $\leq 1\%$, $t_w = 10\ \mu\text{s}$</p>	—	5	—	ns
	Turn-ON time	t_{on}		—	11	—	
	Fall time	t_f		—	3	—	
	Turn-OFF time	t_{off}		—	18	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} = 32\text{ V}, V_{GS} = 10\text{ V}, I_D = 30\text{ A}$	—	22	—	nC
			$V_{DD} = 32\text{ V}, V_{GS} = 5\text{ V}, I_D = 30\text{ A}$	—	12	—	
Gate-source charge 1		Q_{gs1}	$V_{DD} = 32\text{ V}, V_{GS} = 10\text{ V}, I_D = 30\text{ A}$	—	5.1	—	
Gate-drain ("miller") charge		Q_{gd}		—	4.9	—	
Gate switch charge		Q_{sw}		—	7.4	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	90	A
Forward voltage (diode)		V_{DSF}	$I_{DR} = 30\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.2	V

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